

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	81700	@pd<"20020602"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:10
		@pd<"20020602"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:10
		S49	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:08
		capacitor and surface near roughness and capacitance near density and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 14:58
		capacitor and barium near strontium near titanium near oxide and S20 and surface near roughness near S21 ra	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 14:42
		"5,967,795" 5,712,503; Ueno, et "al.", U.S. "Pat." "No." "5,789,311"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:45
		SOI or semiconductor-on-insulator or silicon-on-insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:45
L2	22396	(field near (plate or electrode)) or (field near relief near electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:46

EAST Search History

L3	89547	bipolar near3 transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:46
L4	221	I1 and I2 and I3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:46
L5	81149	soi or silicon-on-insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:46
L6	1798	lateral near bipolar near2 transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:47
L7	17397	(field near plate) or (shield\$3 near5 electrostatic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:47
L8	7	I5 and I6 and I7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:47
L9	429	I5 and I6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:47
L10	38	I5 and I6 and electrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:47

EAST Search History

L11	3821	257/355,361,362,367,511,e29.182, e29.184,e29.187.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:48
L12	30	(@ad<"20020604" @rlad<"20020604") and l10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:48
L13	6	(@ad<"20020604" @rlad<"20020604") and l8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:48
L14	341	(@ad<"20020604" @rlad<"20020604") and l9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:49
L15	87	l14 and l11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:54
L16	5	l13 and l11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:54
L17	9	l12 and l11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/29 10:54
S1	5479	filed near (shield plate relief)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:42

EAST Search History

S2	10331	field near (shield plate relief)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 17:52
S3	67783	soi or (silicon near on near insulator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 17:52
S4	546	S2 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 17:52
S5	362	S4 and @ad<"20020604"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 17:58
S6	304	S4 and metal\$8 and (@ad<"20020604" or @rlad<"20020604")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 18:02
S7	298	S4 and metal\$8 and (@ad<"20020604" or @rlad<"20020604") and between	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 18:02
S8	39	("4065781" "4091527" "4309715" "4313809" "4507846" "4700454" "4766482" "4778775" "4907053").PN. OR ("4996575").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/25 18:04

EAST Search History

S9	48	("20010030722" "20020080295" "20020093019" "20030038303" "4609930" "4748485" "4977105" "4984033" "4996575" "5034788" "5103277" "5124769" "5140391" "5185535" "5198379" "5233211" "5246882" "5273921" "5275972" "5281840" "5294821" "5315132" "5327001" "5359219" "5371398" "5420048" "5463483" "5470793" "5475238" "5485019" "5506436" "5521107" "5532850" "5580802" "5604368" "5621224" "5646424" "5702963" "5807772" "5818076" "5917221" "6054734" "6225150" "6252248" "6323068" "6330044" "6479333" "6603453").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/25 18:28
S10	14	(S9 S8 S7) and adhesive	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/25 18:29
S11	2	("5198379").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/26 11:47
S12	5506	filed near (shield plate relief)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:43
S13	10762	field near (shield plate relief)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:43
S14	73294	soi or silicon-on-insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:43

EAST Search History

S15	17576	bipolar same (pnp or npn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:32
S16	1028	S14 and S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:44
S17	72	S16 and (field near (plate or electrode or conductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:48
S18	813	S16 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:45
S19	8246	257/347,350,351,526,E27.112,E29.009,E29.01,E29.182,E29.184.ccls.438/152,155.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:46
S20	22788584	@ad<"20020604" @rlad<"20020604"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:46
S21	57	S17 and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:46
S22	51	S16 and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:48

EAST Search History

S23	78	S22 and I9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 12:48
S24	38	S22 and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:00
S25	557	(field near plates) same (double multiple second two) and (bipolar bjt) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:00
S26	603	(field near plates) same (double multiple second two) and (bipolar bjt pnp npn) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:09
S27	113	(field near plates) same (double multiple second two) same (bipolar bjt pnp npn) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:09
S28	626	(field near plates metallization) same (double multiple second two) same (bipolar bjt pnp npn) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:09
S29	2	"5198379".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:11
S30	0	filed near plate and electrically near shield and (bjt bipolar near transistor) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:11

EAST Search History

S31	0	filed near plates and electrically near shield and (bjt bipolar near transistor) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:11
S32	0	filed near plates same electrically near shield and (bjt bipolar near transistor) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:12
S33	0	field near plates same electrically near shield and (bjt bipolar near transistor) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:13
S34	16	electrically near shield and (bjt bipolar near transistor) and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:18
S35	33732	pnp near transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:18
S36	1	pnp near transistor and filed near plates	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:19
S37	192	pnp near transistor and field near plates	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:19
S38	153	pnp near transistor and field near plates and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:30

EAST Search History

S39	2	("6252248").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/21 13:32
S40	11531	(bipolar same (pnp or npn)) near transistor bjt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:33
S41	11	((("6190948") or ("5420457") or ("5440161") or ("5731627") or ("5973341") or ("6118154"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/21 13:34
S42	6	((("6190948") or ("5420457") or ("5440161") or ("5731627") or ("5973341") or ("6118154"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/09/21 13:36
S43	1	filed near plate and bjt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:36
S44	42	field near plate and bjt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 13:41
S45	0	capacitor and barium near strontium near titanium near oxide and S20 and surface near roughness near10 ra	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 14:43
S46	15	capacitor and barium near strontium near titanium near oxide and S20 and surface near roughness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 14:57

EAST Search History

S47	104	capacitor and surface near roughness and capacitance near density	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/21 14:58
S48	22841012	@ad<"20020602" @rlad<"20020602"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 14:50
S49	22841012	@ad<"20020602" @rlad<"20020602"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:09
S50	22837812	@ad<"20020604" @rlad<"20020504"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:09
S51	22841012	@ad<"20020602" @rlad<"20020602"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:09
S52	30337582	@pd<"20020602"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:11
S53	22846531	@ad<"20020604" @rlad<"20020604"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:11
S54	2	"6335540".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:16

EAST Search History

S55	2	"5886364".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 15:16
S56	1	"5886364".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/03/07 16:53
S57	36	"5916642"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/03/07 16:53
S58	2	("5916642").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/07 17:24
S59	1938	amorphous near graphite	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 17:25
S60	93	amorphous near graphite and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 18:09
S61	17	crystalline near shell and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 18:10